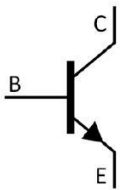


Silicon NPN transistor in a TO-18 Plastic Package.

Complementary pair with BD234.

Medium power linear and switching applications.

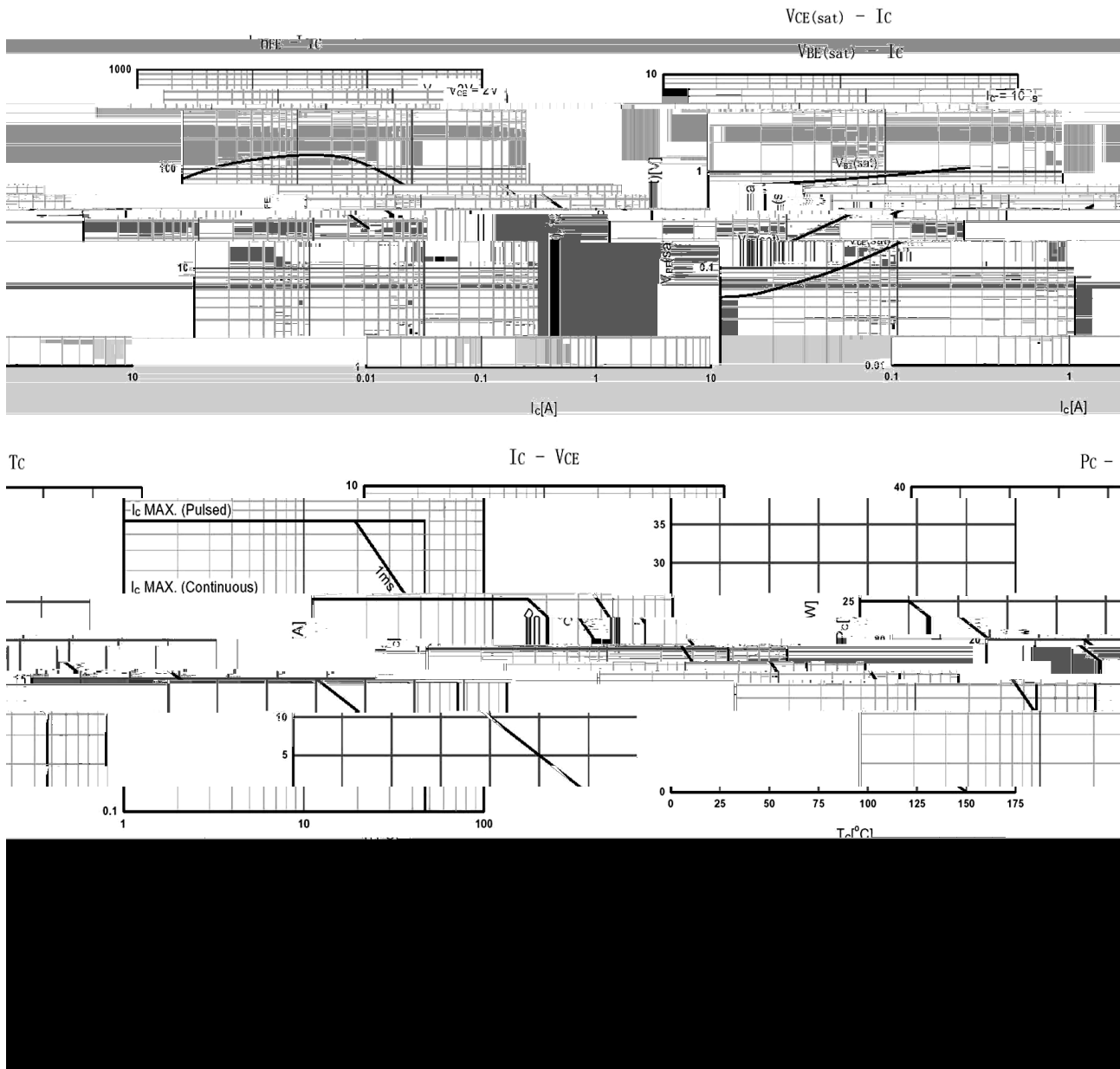


PIN1 Emitter PIN 2 Collector PIN 3 Base

See Marking Instructions

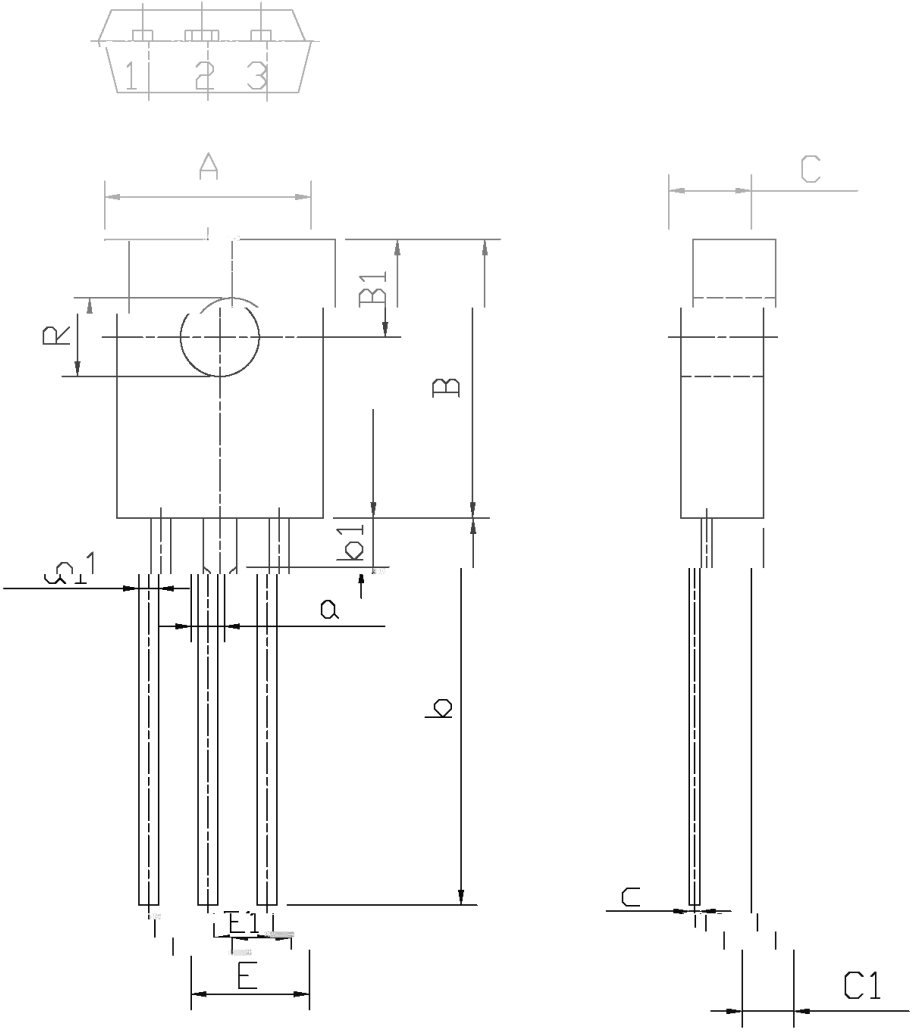
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	45	V
Collector to Emitter Voltage	V_{CEO}	45	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	2.0	A
Collector Current – Continuous(Pulse)	I_{CP}	6.0	A
Collector Power Dissipation	P_C	1.0	W
Collector Power Dissipation	$P_C(T_c=25^\circ C)$	25	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=100mA$ $I_B=0$	45			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=45V$ $I_E=0$			100	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=5.0V$ $I_C=0$			1.0	mA
DC Current Gain	$h_{FE(1)}$	$V_{CE}=2.0V$ $I_C=150mA$	40		400	
	$h_{FE(2)}$	$V_{CE}=2.0V$ $I_C=1.0A$	25			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=1.0A$ $I_B=0.1A$			0.6	V
Base to Emitter Voltage	V_{BE}	$V_{CE}=2.0V$ $I_C=1.0A$			1.3	V
Transition Frequency	f_T	$V_{CE}=10V$ $I_C=250mA$	3.0			MHz

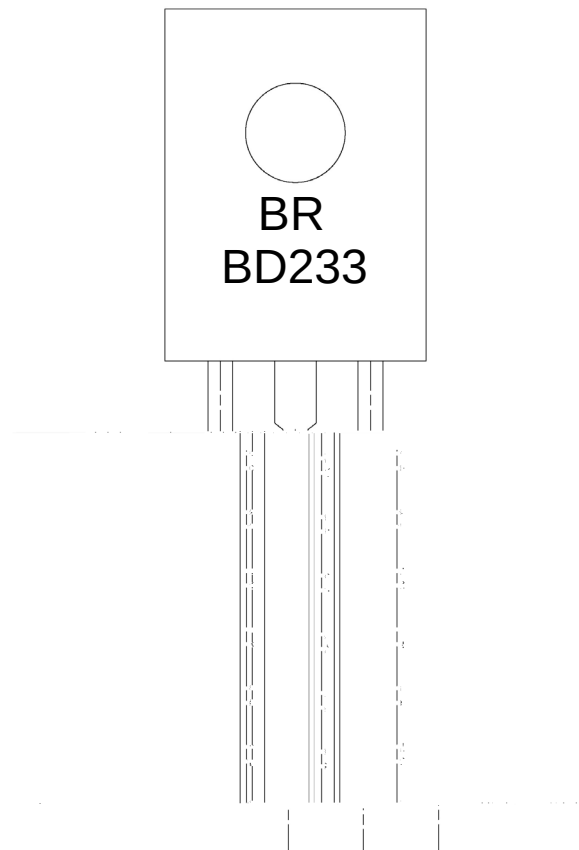


FW-126T

单位: mm



Symbol	Dimension in Millimeters		Symbol	Dimension in Millimeters	
	Min	Max		Min	Max
A	7.8	8.2	a1	0.45	0.85
B	10.0	11.2	E	4.4	4.8
B1	3.8	4.2	C	3.1	3.3
R	2.05	3.15	C1	1.9	2.1
b	14	16	c	0.3	0.6
b1	1.9		a	1.27	
E1	2.1	2.5			

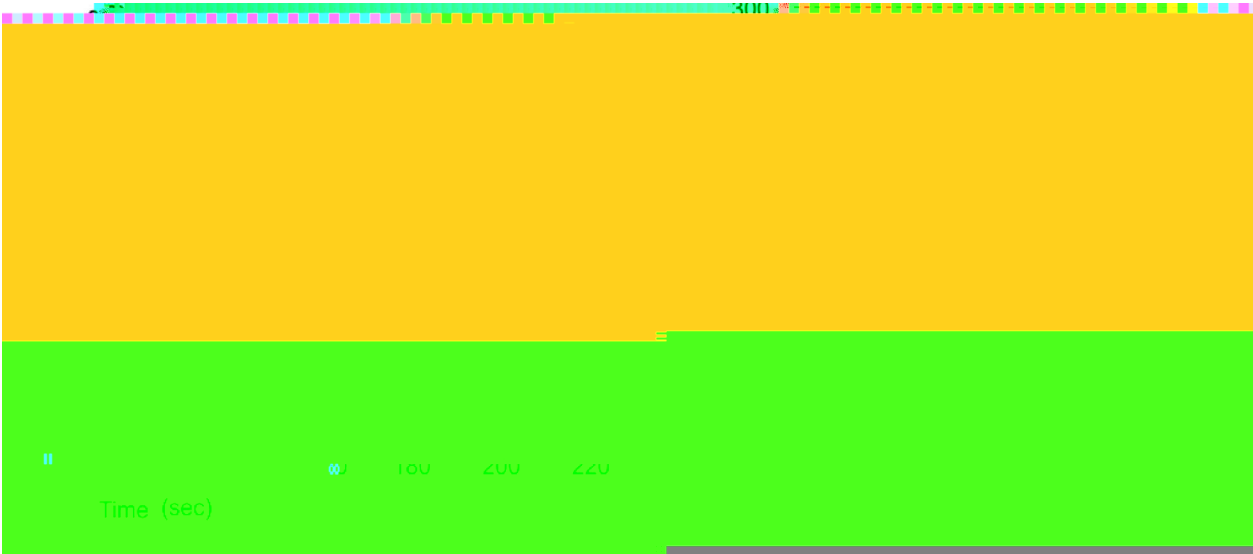


Note:

BR: Company Code

BD233: Product Type.

****: Lot No. Code, code change with Lot No.



				Note:
1	25	150	60 90sec;	1.Preheating:25~150 , Time:60~90sec.
2	255	5	5 0.5sec;	2.Peak Temp.:255 5 , Duration:5 0.5sec.
3				